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LEE(10) **Pub. No.: US 2024/0251562 A1**(43) **Pub. Date: Jul. 25, 2024**(54) **SEMICONDUCTOR DEVICE AND METHOD
OF MANUFACTURING THE SAME****Publication Classification**(71) Applicant: **SK hynix Inc.**, Icheon-si Gyeonggi-do
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ABSTRACT

A semiconductor device and a method of manufacturing a semiconductor device may be provided. The semiconductor device may include first and second vertical conductive patterns isolated from each other by a first slit. The semiconductor device may include at least one first half conductive pattern extending toward a first region disposed at one side of the first slit from the first vertical conductive pattern. The semiconductor device may include at least one second half conductive pattern extending toward a second region disposed at the other side of the first slit from the second vertical conductive pattern.

